

Features

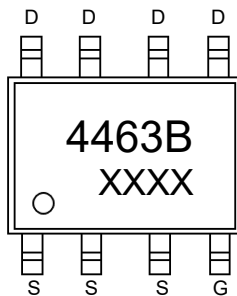
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-20V	7m Ω @-10V	-18.6A
	8.5m Ω @-4.5V	

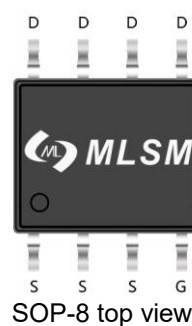
Application

- Adaptor switch
- High current load switch
- Notebook

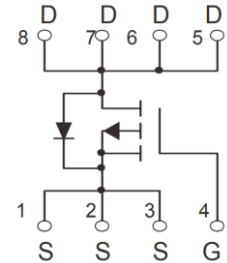


Marking and pin assignment

4463B : Device code
 XXXX : Code



SOP-8 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±12	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-18.6	A

Mounted on Large Heat Sink

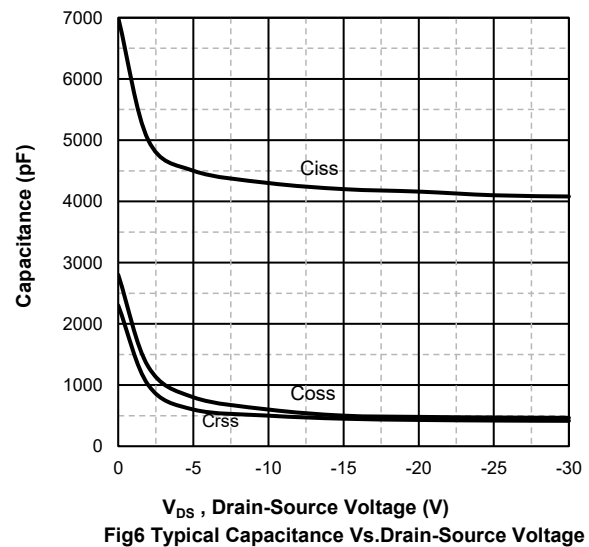
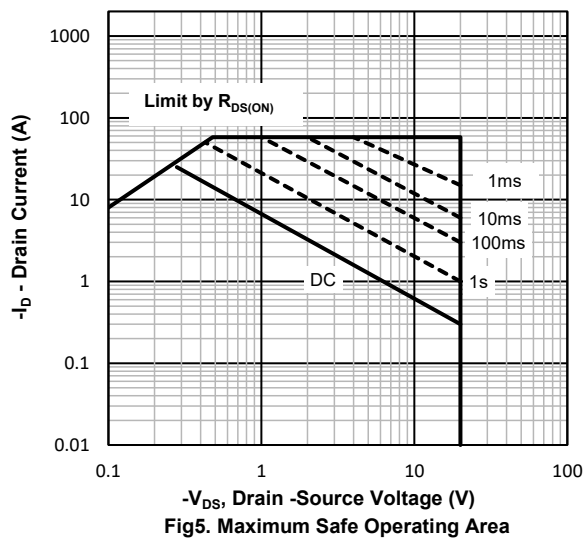
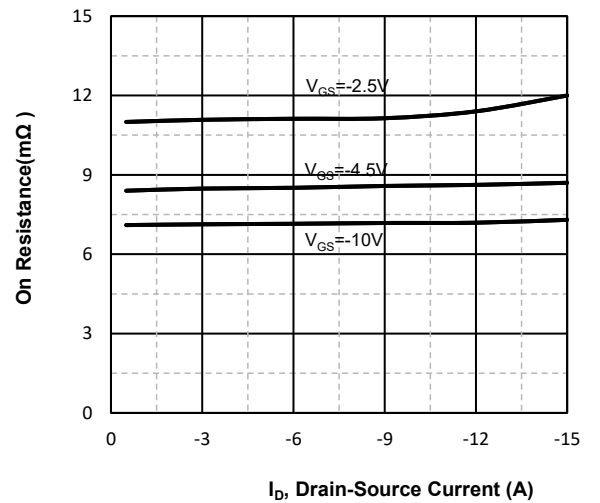
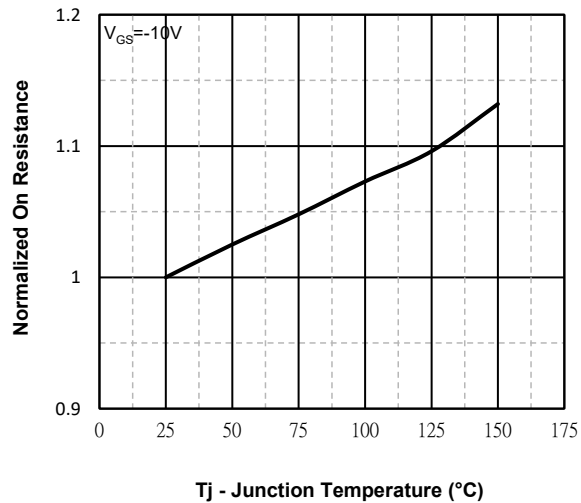
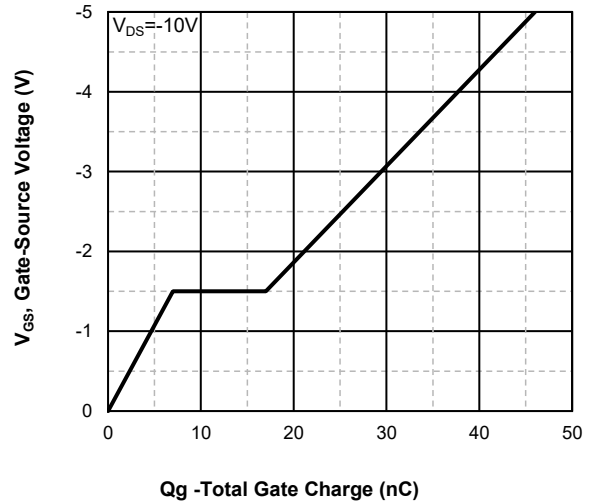
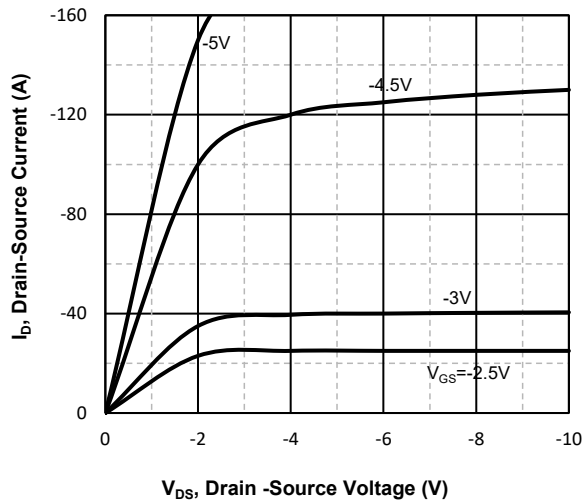
I_{DM}	Pulse Drain Current Tested	Tc=25°C	-58	A
I_D	Continuous Drain Current	Tc=25°C	-18.6	A
P_D	Maximum Power Dissipation	Tc=25°C	5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		45	°C/W

Ordering Information (Example)

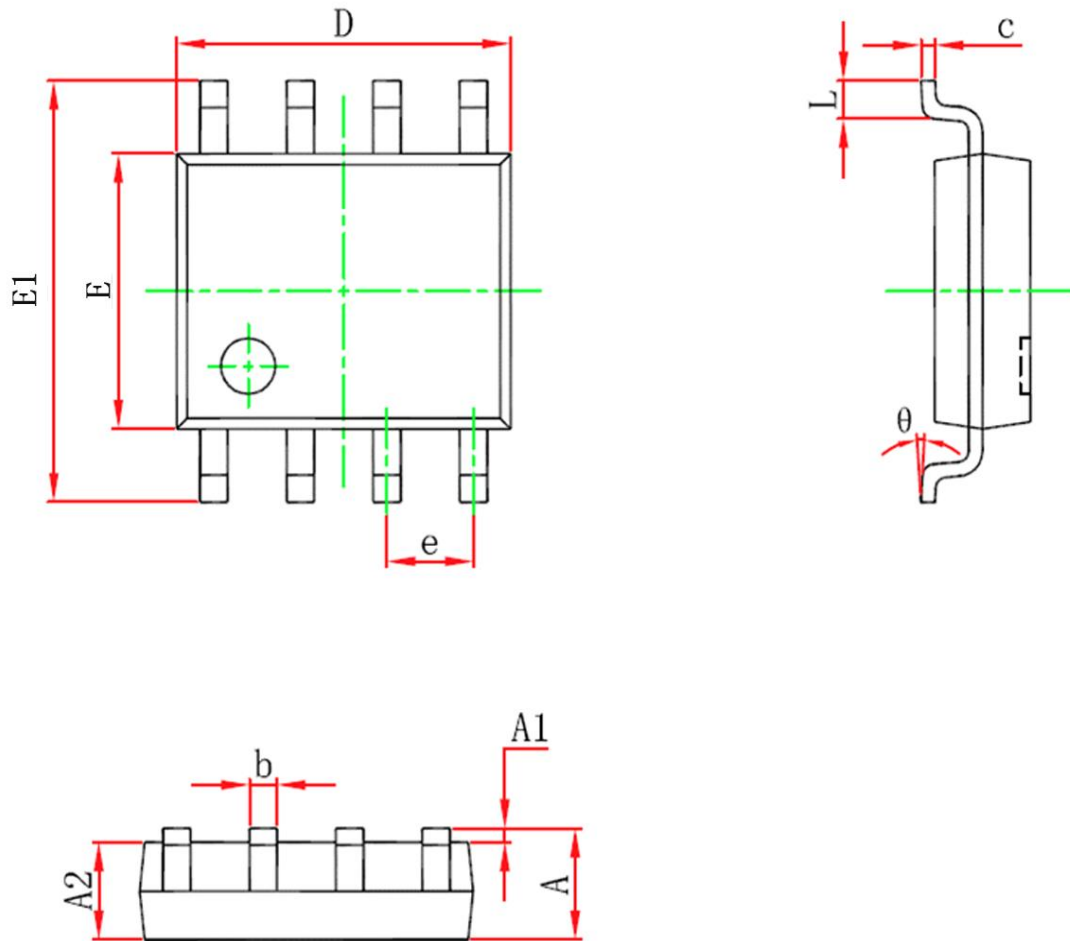
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSQ4463B	SOP-8	4463B	3,000	6,000	42,000	13"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	—	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	—	—	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	—	—	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	-0.6	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-13A	—	7	8	mΩ
		V _{GS} =-4.5V, I _D =-12A	—	8.5	11	mΩ
		V _{GS} =-2.5V, I _D =-5A	—	11	14	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	—	4550	--	pF
C _{OSS}	Output Capacitance		—	500	--	pF
C _{RSS}	Reverse Transfer Capacitance		—	450	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-18.6A, V _{GS} =-4.5V	—	45	--	nC
Q _{gs}	Gate Source Charge		—	7	--	nC
Q _{gd}	Gate Drain Charge		—	11	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-18.6A, V _{GS} =-10V, R _G =3Ω	--	8	--	nS
t _r	Turn-on Rise Time		—	60	--	nS
t _{d(off)}	Turn-Off Delay Time		—	110	--	nS
t _f	Turn-Off Fall Time		—	45	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =-18.6A	—	-0.8	-1.2	V

Typical Operating Characteristics



SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°